N-Channel Silicon MOSFET

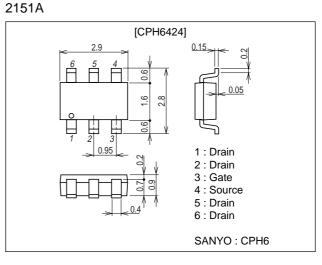


## Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

# **Package Dimensions**

unit : mm



# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

| Parameter                   | Symbol | Conditions  | Ratings     | Unit |
|-----------------------------|--------|---|-------------|------|
| Drain-to-Source Voltage     | VDSS   |   | 60          | V    |
| Gate-to-Source Voltage      | VGSS   |   | ±20         | V    |
| Drain Current (DC)          | ۱D     |   | 3           | А    |
| Drain Current (Pulse)       | IDP    | PW≤10µs, duty cycle≤1%                                  | 12          | А    |
| Allowable Power Dissipation | PD     | Mounted on a ceramic board (1200mm <sup>2</sup> X0.8mm) | 1.6         | W    |
| Channel Temperature         | Tch    |   | 150         | °C   |
| Storage Temperature         | Tstg   |   | -55 to +150 | °C   |

## Electrical Characteristics at Ta=25°C

| Symbol                | Conditions  | Ratings  |   |  | Unit   |
|-----------------------|---|--|---|--|--|
|                       |   | min  | typ   | max  | Unit   |
| V(BR)DSS              | ID=1mA, VGS=0   | 60   |   |  | V  |
| IDSS                  | V <sub>DS</sub> =60V, V <sub>GS</sub> =0                  |  |   | 1  | μΑ   |
| IGSS                  | V <sub>GS</sub> =±16V, V <sub>DS</sub> =0                 |  |   | ±10  | μA   |
| VGS(off)              | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA                 | 1.2  |   | 2.6  | V  |
| yfs                   | V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A                | 2.3  | 3.4   |  | S  |
| R <sub>DS</sub> (on)1 | ID=1.5A, VGS=10V  |  | 110   | 145  | mΩ   |
| R <sub>DS</sub> (on)2 | ID=1.5A, VGS=4V   |  | 150   | 215  | mΩ   |
|                       | V(BR)DSS<br>IDSS<br>IGSS<br>VGS(off)<br> yfs <br>RDS(on)1 | V(BR)DSS ID=1mA, VGS=0   IDSS VDS=60V, VGS=0   IGSS VGS=16V, VDS=0   VGS(off) VDS=10V, ID=1mA    yfs  VDS=10V, ID=1.5A   RDS(on)1 ID=1.5A, VGS=10V | V(BR)DSS ID=1mA, VGS=0 60   IDSS VDS=60V, VGS=0 60   IGSS VGS=±16V, VDS=0 1.2   VGS(off) VDS=10V, ID=1mA 1.2    yfs  VDS=10V, ID=1.5A 2.3   RDS(on)1 ID=1.5A, VGS=10V 1.2 | Symbol Conditions min typ   V(BR)DSS ID=1mA, VGS=0 60 60   IDSS VDS=60V, VGS=0 60 60   IGSS VGS=416V, VDS=0 60 60   VGS(off) VDS=10V, ID=1mA 1.2 1.2   Iyfs VDS=10V, ID=1.5A 2.3 3.4   RDS(on)1 ID=1.5A, VGS=10V 110 110 | Symbol Conditions min typ max   V(BR)DSS ID=1mA, VGS=0 60 1   IDSS VDS=60V, VGS=0 1 1   IGSS VGS=±16V, VDS=0 1 ±10   VGS(off) VDS=10V, ID=1mA 1.2 2.6    yfs  VDS=10V, ID=1.5A 2.3 3.4   RDS(on)1 ID=1.5A, VGS=10V 110 145 |

Marking : ZA

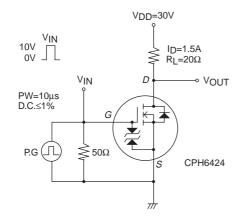
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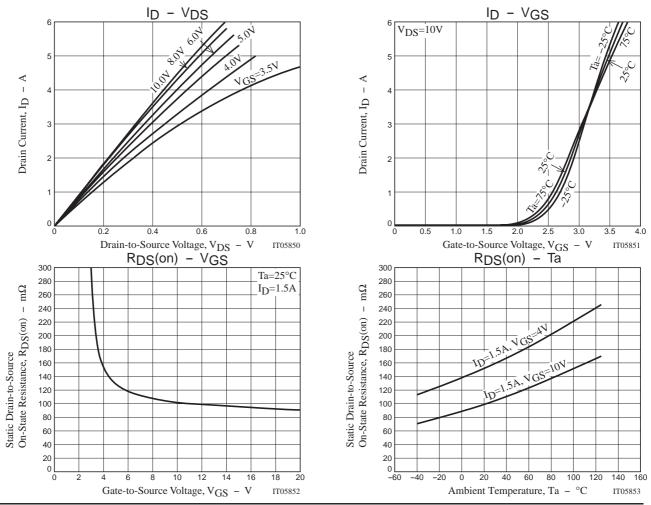
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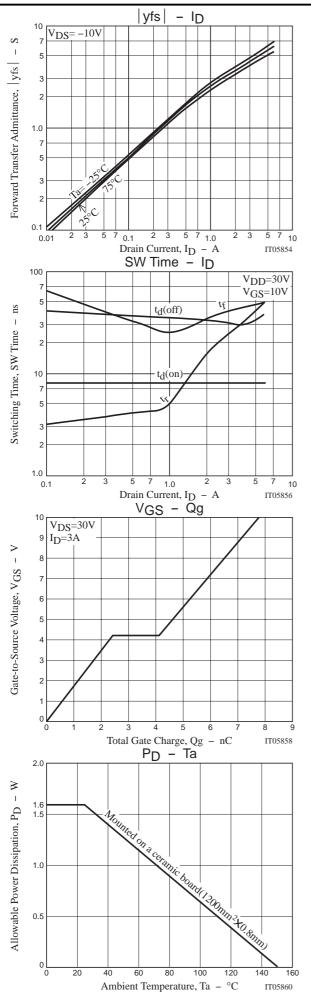
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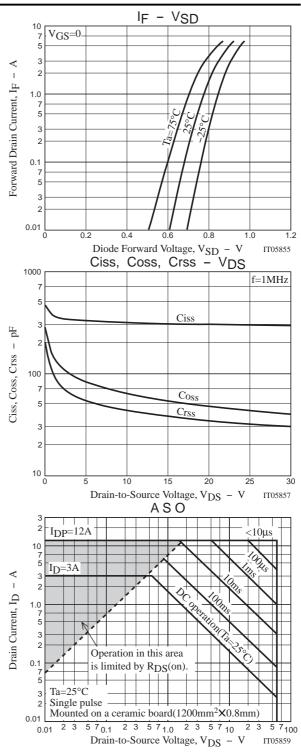
| Parameter                     | Symbol              | Conditions   |     | Ratings |     |      |
|-------------------------------|---------------------|--|-----|---------|-----|------|
|                               | Symbol              |  | min | typ     | max | Unit |
| Input Capacitance             | Ciss                | V <sub>DS</sub> =20V, f=1MHz                                   |     | 266     |     | pF   |
| Output Capacitance            | Coss                | V <sub>DS</sub> =20V, f=1MHz                                   |     | 54      |     | pF   |
| Reverse Transfer Capacitance  | Crss                | VDS=20V, f=1MHz  |     | 34      |     | pF   |
| Turn-ON Delay Time            | t <sub>d</sub> (on) | See specified Test Circuit.                                    |     | 8       |     | ns   |
| Rise Time                     | tr                  | See specified Test Circuit.                                    |     | 8       |     | ns   |
| Turn-OFF Delay Time           | td(off)             | See specified Test Circuit.                                    |     | 33      |     | ns   |
| Fall Time                     | tf                  | See specified Test Circuit.                                    |     | 30      |     | ns   |
| Total Gate Charge             | Qg                  | V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A |     | 7.8     |     | nC   |
| Gate-to-Source Charge         | Qgs                 | V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A |     | 2.4     |     | nC   |
| Gate-to-Drain "Miller" Charge | Qgd                 | V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A |     | 1.7     |     | nC   |
| Diode Forward Voltage         | VSD                 | IS=3A, VGS=0   |     | 0.84    | 1.2 | V    |

### **Switching Time Test Circuit**









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